Solid State Devices, Inc.
14701 Firestone Blvd * La Mirada, Ca 90638
Phone: (562) 404-4474 * Fax: (562) 404-1773
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SFX1192

DESIGNER'S DATA SHEET

Part Number / Ordering Information [1/]

SFX1192

Screening [2/]
__ = Not Screened
TX = TX Level
TXV = TXV Level
S = S Level

Package
__ = TO-5

2 AMP
PNP TRANSISTOR
500 VOLTS

Features:
- BV_{CEO} 400 Volts
- Fast Switching
- High Frequency
- Low Saturation Voltage
- 200ºC Operating Temperature
- Designed for Complementary Use with SFT6800
- TX, TXV, S-Level Screening Available [2/] - Consult Factory

Maximum Ratings [3/]	Symbol	Value	Units
Collector – Emitter Voltage	V_{CEO}	500	Volts
Collector – Base Voltage	V_{CBO}	600	Volts
Emitter – Base Voltage	V_{EBO}	10	Volts
Collector Current	I_C	2	Amps
Base Current	I_B	0.5	Amps
Total Device Dissipation @ TC = 100ºC Derate above 100ºC	P_D	6 150	W mW/ºC
Operating & Storage Temperature	Top & Tstg	-65 to +200	ºC
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	15	ºC/W

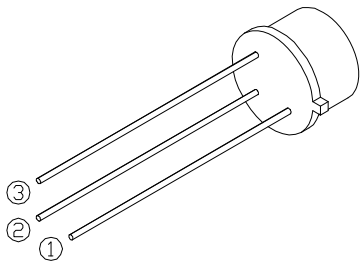
NOTES:
* Pulse Test: Pulse Width = 300µsec, Duty Cycle = 2%

1/ For ordering information, price, operating curves, and availability - Contact factory.

2/ Screening based on MIL-PRF-19500. Screening flows available on request.

3/ Unless Otherwise Specified, All Electrical Characteristics @25ºC.

TO-5



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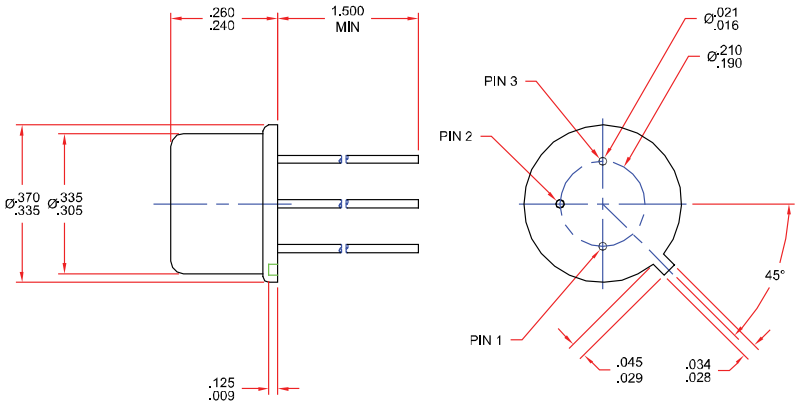
Electrical Characteristic [4/]		Symbol	Min	Max	Units
Collector – Emitter Breakdown Voltage*	I_C = 5mA	**BV_{CEO}**	400	—	Volts
Collector – Base Breakdown Voltage	I_C = 100µA	**BV_{CBO}**	500	—	Volts
Emitter – Base Breakdown Voltage	I_E = 20µA	**BV_{EBO}**	10	—	Volts
Collector – Cutoff Current	V_{CB} = 450V	**I_{CBO}**	—	1.0	µA
Collector – Cutoff Current	V_{CE} = 400V, V_{EB} = 1.5V	**I_{CEV}**	—	10	µA
Emitter – Cutoff Current	V_{EB} = 6V	**I_{EBO}**	—	10	µA
DC Current Gain * (V_{CE} = 10V)	I_C = 1.0mA I_C = 50mA I_C = 500mA	**h_{FE}**	80 60 40	— — —	—
Collector – Emitter Saturation Voltage *	I_C = 50mA, I_B = 5mA I_C = 500mA, I_B = 50mA	**$V_{CE(Sat)}$**	— —	0.4 1.0	Volts
Base – Emitter Saturation Voltage *	I_C = 50mA, I_B = 5mA I_C = 500mA, I_B = 50mA	**$V_{BE(Sat)}$**	— —	1.5 2.0	Volts
Current Gain Bandwidth Product	V_{CE} = 30V, I_C = 70mA, f = 20MHz	**f_T**	50	—	MHz
Output Capacitance	V_{CB} = 20V, I_E = 0A, f = 1MHz	**C_{ob}**	—	75	pF
Input Capacitance	V_{BE} = 2V, I_C = 0A, f = 1MHz	**C_{ib}**	—	300	pF
Turn On Time	V_{CC} = 100V, $V_{EB(Off)}$ = 3.7V I_C = 500mA I_{B1} = I_{B2} = 50mA	**t_{ON}**	—	250	nsec
Turn Off Time		**t_{OFF}**	—	2500	nsec

TO-5



PIN ASSIGNMENT

Package	Pin 1	Pin 2	Pin 3 (Case)
TO-5	Emitter	Base	Collector

NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: TR0111A | **DOC**